

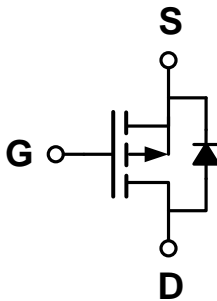
## DESCRIPTION

The LXP1612B uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and high density cell Design for ultra low on-resistance. This device is suitable for use as a load switch or in PWM applications

## APPLICATION

- PWM applications
- Load switch

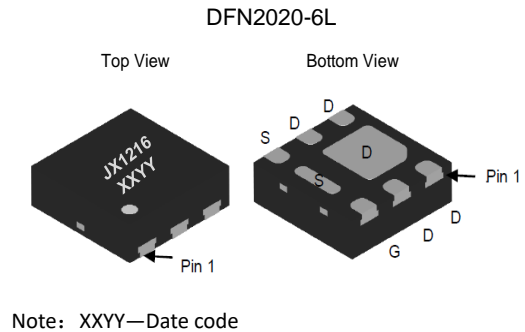
## SCHEMATIC DIAGRAM



## GENERAL FEATURES

- $V_{DS} = -12V$ ,  $I_D = -16A$   
 $R_{DS(ON)}(Typ.) = 16.5m\Omega @ V_{GS} = -2.5V$   
 $R_{DS(ON)}(Typ.) = 12m\Omega @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

## PIN ASSIGNMENT



## ORDERING INFORMATION

Part Number	Storage Temperature	Package	Marking	Devices Per Reel
LXP1612B	-55°C to +150°C	DFN2020-6L	JX1216 XXYY	3000

## ABSOLUTE MAXIMUM RATINGS

( $T_A = 25^\circ C$  unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	$V_{DS}$	-12	V
Gate-source voltage	$V_{GS}$	$\pm 12$	V
Drain current-continuous	$I_D$	$T_C = 25^\circ C$	-16 <sup>a</sup>
		$T_C = 70^\circ C$	-16 <sup>a</sup>
		$T_A = 25^\circ C$	-16 <sup>a,b,c</sup>
		$T_A = 70^\circ C$	-12 <sup>b,c</sup>
Drain-source Diode forward current	$I_S$	$T_C = 25^\circ C$	-16 <sup>a</sup>
		$T_A = 25^\circ C$	-2.9 <sup>b,c</sup>
Maximum power dissipation	$P_D$	$T_C = 25^\circ C$	18
		$T_C = 70^\circ C$	12
		$T_A = 25^\circ C$	3.5 <sup>b,c</sup>
		$T_A = 70^\circ C$	2.2 <sup>b,c</sup>
Operating junction Temperature range	$T_J$	-55~150	°C



## THERMAL CHARACTERISTICS

Parameter	Symbol	Typ.	Max.	Unit	
Maximum junction-to-ambient <sup>b,d</sup>	$t \leq 5 \text{ s}$	$R_{thJA}$	28	36	°C
Maximum junction-to-case (drain)	Steady state	$R_{thJC}$	5.3	6.5	

Notes:

- a. Package limited; b. Surface mounted on 1" x 1" FR4 board  
c.  $t = 5 \text{ s}$ ; d. Maximum under steady state conditions is 80 °C/W

## ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF Characteristics</b>						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-12	-16.5	-	V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=-12V, V_{GS}=0V$	-	-	-1	$\mu A$
Gate-body leakage	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	$\pm 100$	nA
<b>ON Characteristics</b>						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.45	-0.68	-1.2	V
Drain-source on-state resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-8A$	-	12	15	m $\Omega$
		$V_{GS}=-2.5V, I_D=-6A$	-	16.5	23	
Forward transconductance	$g_{fs}$	$V_{DS}=-6V, I_D=-7A$	-	32	-	S
<b>Dynamic Characteristics</b>						
Input capacitance	$C_{ISS}$	$V_{DS}=-6V, V_{GS}=0V$ $f=1.0\text{MHz}$	-	1300	-	pF
Output capacitance	$C_{OSS}$		-	380	-	
Reverse transfer capacitance	$C_{RSS}$		-	280	-	
<b>Switching Characteristics</b>						
Turn-on delay time	$t_{D(ON)}$	$V_{DD}=-10V$ $I_D=-5A$ $V_{GEN}=-4.5V$ $R_L=1 \text{ } \Omega, 2\text{ohm}$ $R_{GEN}=1\text{ohm}$	-	11	-	ns
Rise time	$t_r$		-	35	-	
Turn-off delay time	$t_{D(OFF)}$		-	30	-	
Fall time	$t_f$		-	10	-	
Total gate charge	$Q_g$	$V_{DS}=-6V, I_D=-9A$ $V_{GS}=-4.5V$	-	13	-	nC
Gate-source charge	$Q_{gs}$		-	3	-	
Gate-drain charge	$Q_{gd}$		-	5	-	
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Diode forward voltage	$V_{SD}$	$V_{GS}=0V, I_S=-1.25A$	-	-0.7	-1.2	V

Notes:

- a. Pulse test: Pulse width  $\leq 300 \mu s$ , duty cycle  $\leq 2 \%$   
b. Guaranteed by design, not subject to production testing

**TYPICAL PERFORMANCE CHARACTERISTICS**

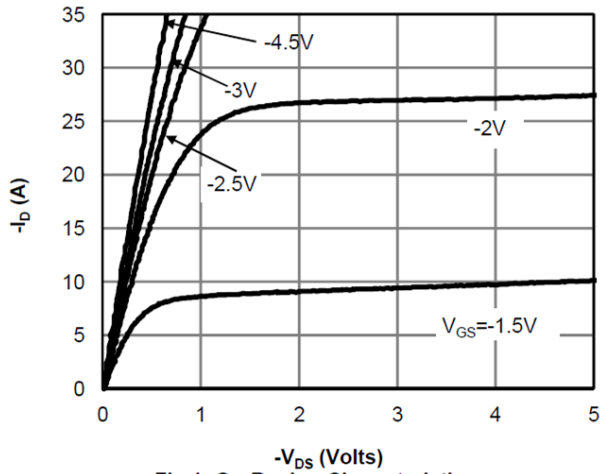


Fig 1: On-Region Characteristics

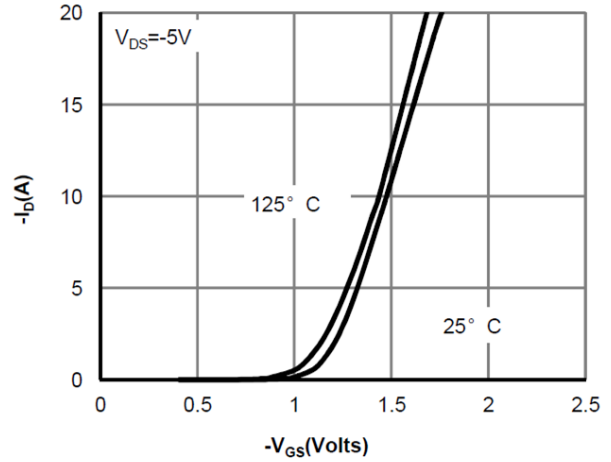


Figure 2: Transfer Characteristics

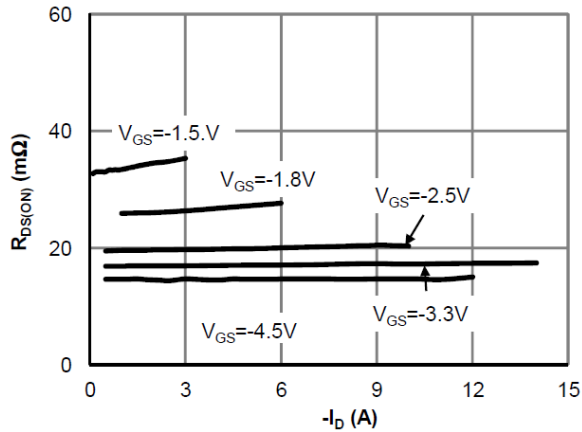


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

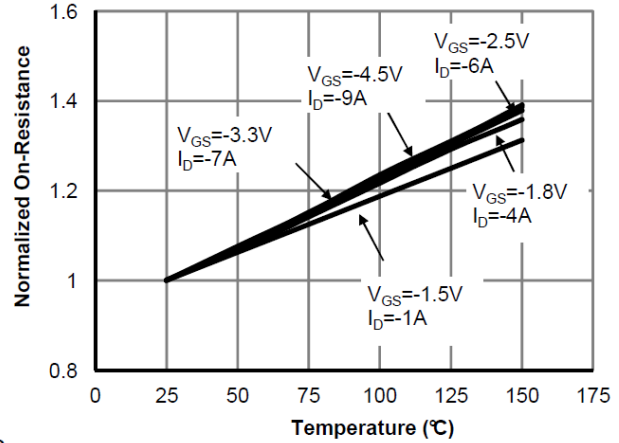


Figure 4: On-Resistance vs. Junction Temperature

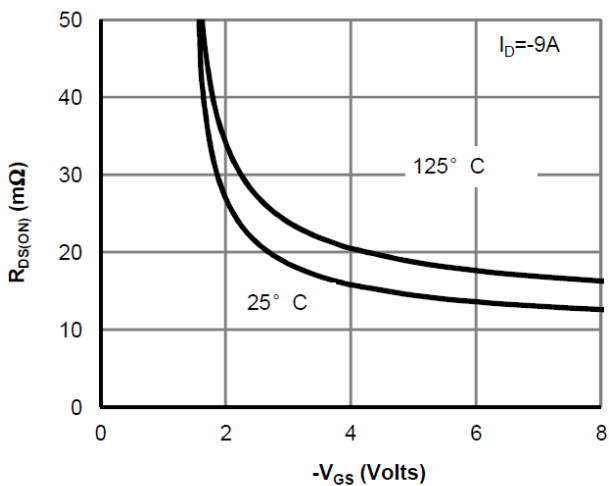


Figure 5: On-Resistance vs. Gate-Source Voltage

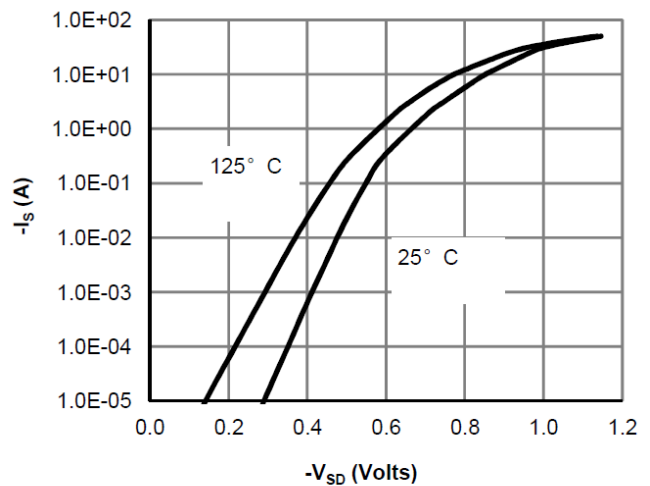


Figure 6: Body-Diode Characteristics

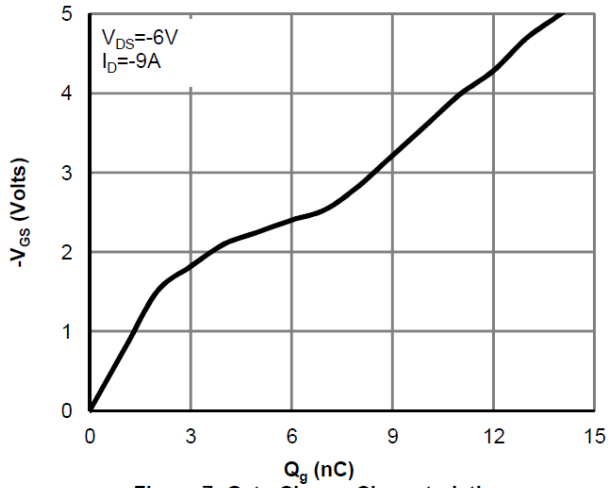


Figure 7: Gate-Charge Characteristics

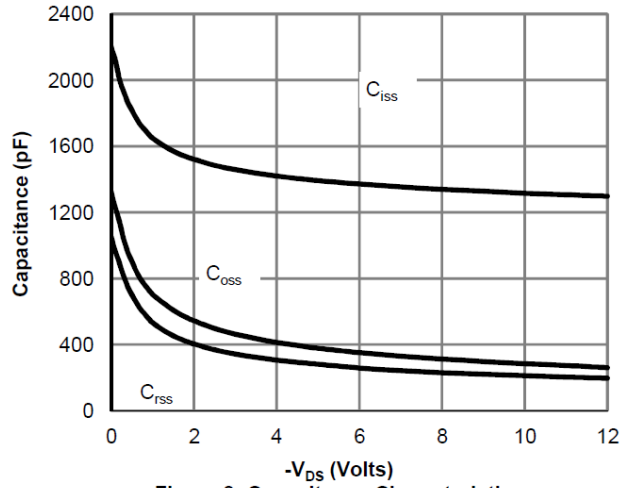


Figure 8: Capacitance Characteristics

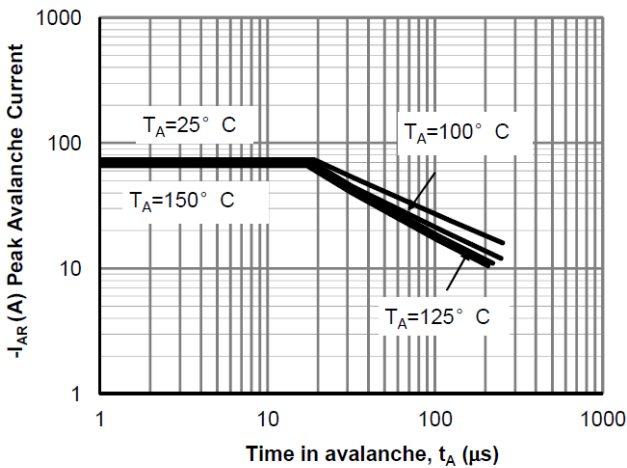


Figure 9: Single Pulse Avalanche capability

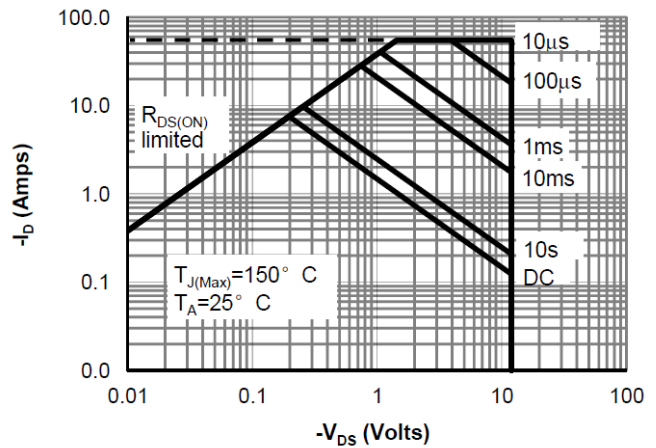


Figure 10: Maximum Forward Biased Safe Operating Area

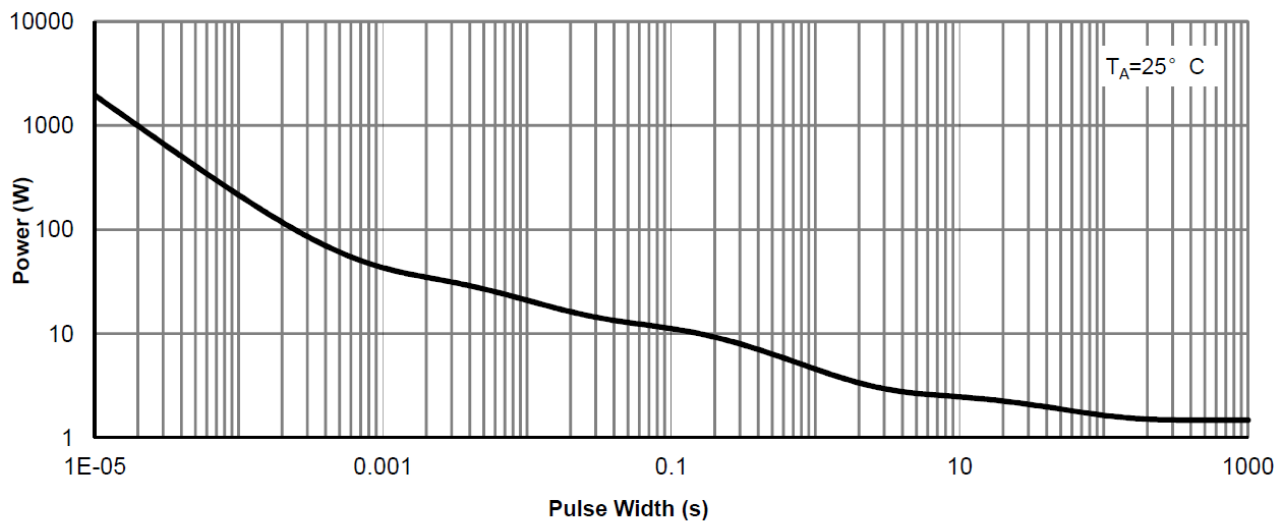


Figure 11: Single Pulse Power Rating Junction-to-Ambient

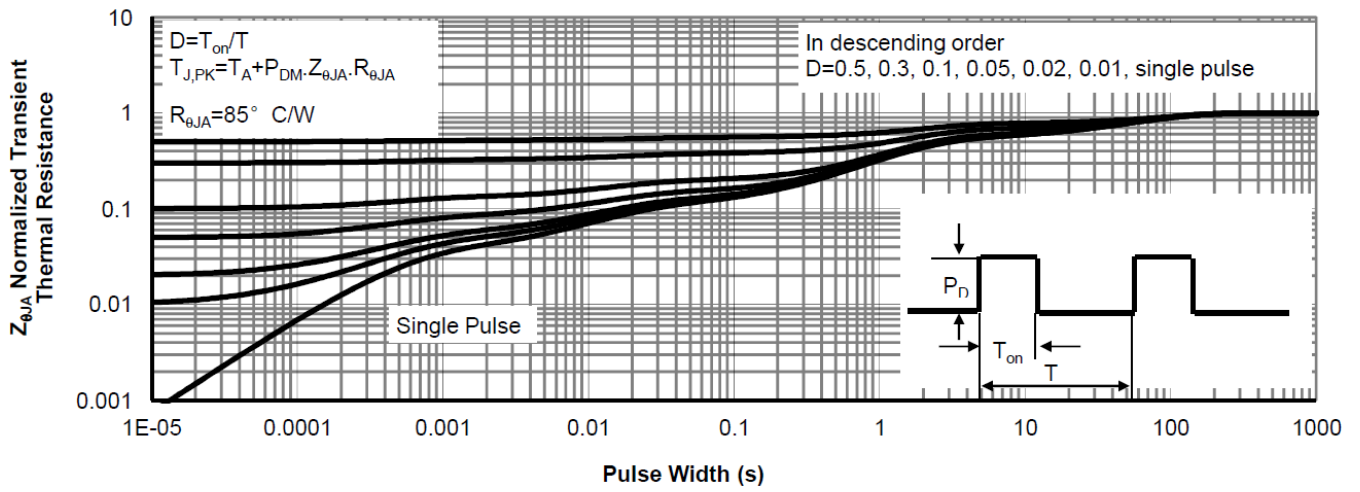
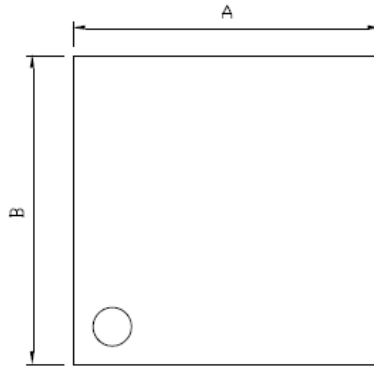
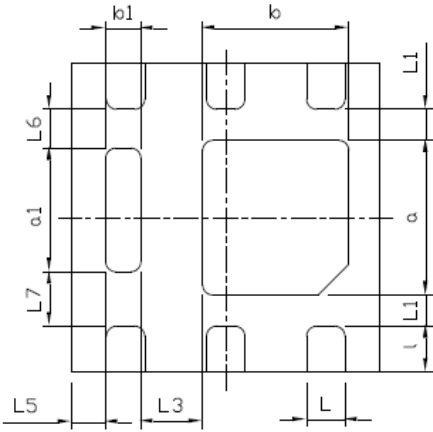


Figure 12: Normalized Maximum Transient Thermal Impedance

**PACKAGE INFORMATION**

● DFN2020-6L



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	1.95	2.00	2.05
B	1.95	2.00	2.05
C	0.45	0.50	0.55
L	0.25	0.30	0.35
L1	0.10	0.20	0.30
L2	-	0.65	-
L3	0.30	0.40	0.50
L4	-	0.152	-
L5	0.12	0.22	0.32
L6	0.15	0.25	0.35
L7	0.23	0.33	0.43
a	0.90	1.00	1.10
a1	0.72	0.82	0.92
b	0.85	0.95	1.05
b1	0.13	0.23	0.33
l	0.25	0.30	0.35
k	0.00	-	0.05

